



PolarHV™ HiPerFET **IXFP 3N50PM Power MOSFET**

(Electrically Isolated Tab)

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Diode

 $V_{DS} = V_{DSS}$

 $V_{GS} = 0 V$

Note 1

 $V_{GS} = 10 \text{ V}, I_{D} = 1.8 \text{ A}$

I_{DSS}

R_{DS(on)}



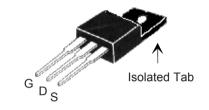
Symbol	Test Conditions	Maximum Ratings		
V _{DSS}	$T_J = 25^{\circ} \text{C to } 150^{\circ} \text{C}$	500	V	
V _{DGR}	$T_J = 25^{\circ} \text{C to } 150^{\circ} \text{C}; R_{GS} = 1 \text{ M}\Omega$	500		
V _{GSS}	Continuous	± 30	V	
V _{GSM}	Transient	± 40		
I _{D25}	$T_{c} = 25^{\circ} C$	2.7	A	
	$T_{c} = 25^{\circ} C$, pulse width limited by T_{JM}	8	A	
I _{AR} E _{AR} E _{AS}	T _c = 25° C	3	A	
	T _c = 25° C	10	mJ	
	T _c = 25° C	100	mJ	
dv/dt	$I_{_{S}} \leq I_{_{DM}}, \text{ di/dt} \leq 100 \text{ A/}\mu\text{s}, V_{_{DD}} \leq V_{_{DSS}}, \\ T_{_{J}} \leq 150^{\circ}\text{ C}, R_{_{G}} = 50 \Omega$	10	V/ns	
P_{D}	T _C = 25° C	36	W	
T _J		-55 +150	°C	
T _{JM}		150	°C	
T _{stg}		-55 +150	°C	
T _L T _{SOLD}	1.6 mm (0.062 in.) from case for 10 s Plastic body for 10 s	300 260	°C	

1.13/10 Nm/lb.in. \mathbf{M}_{d} Mounting torque Weight Symbol **Characteristic Values Test Conditions** (T₁ = 25° C, unless otherwise specified) Min. Typ. Max. $V_{GS} = 0 \text{ V}, I_{D} = 250 \,\mu\text{A}$ ٧ $\mathbf{BV}_{\mathrm{DSS}}$ 500 $V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$ 3.0 ٧ $V_{GS(th)}$ 5.5 $V_{GS} = \pm 30 V_{DC}, V_{DS} = 0$ \mathbf{I}_{GSS} ±100 nΑ

T₁ = 125° C

V _{DSS}	=	500	V
I _{D25}	=	2.7	Α
R _{DS(on)}	≤	2.0	Ω
t _{rr}	≤	200	ns

OVERMOLDED TO-220 (IXTP...M) OUTLINE



G = Gate D = Drain S = Source

Features

- ¹ Plastic overmolded tab for electrical isolation
- Fast intrinsic diode
- International standard package
- Unclamped Inductive Switching (UIS)
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

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5

200

2.0

μΑ

μΑ

Ω



Symbo		Characte 25° C, unless otherw Min. Typ.	ristic Values rise specified) Max.
g _{fs}	$V_{DS} = 10 \text{ V}; I_{D} = 1.8 \text{ A}, \text{ Note 1}$	3.5	S
C _{iss})	409	pF
\mathbf{C}_{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	48	pF
\mathbf{C}_{rss})	6.1	pF
t _{d(on)})	25	ns
t,	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \text{ V}_{DSS}, I_{D} = 3.6 \text{ M}$	A 28	ns
$\mathbf{t}_{d(off)}$	$R_{\rm G} = 50 \Omega $ (External)	63	ns
t _f	J	29	ns
$\mathbf{Q}_{g(on)}$)	9.3	nC
Q_{gs}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \text{ V}_{DSS}, I_{D} = 1.8$	3.3	nC
\mathbf{Q}_{gd}	J	3.4	nC
R _{thJC}			3.5 °C/W

Source-Drain Diode

Characteristic Values (T. = 25° C unless otherwise specified)

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Symbo	l Test Conditions Min.	Тур.	Max.		
Is	$V_{GS} = 0 V$		3.6	Α	
I _{SM}	Repetitive		5	Α	
V _{SD}	$I_F = I_S$, $V_{GS} = 0$ V, Note 1		1.5	V	
t _{rr} Q _{RM} I _{RM}	$\begin{cases} I_{F} = 3.6 \text{ A, -di/dt} = 100 \text{ A/}\mu\text{s,} \\ V_{R} = 100 \text{ V, V}_{GS} = 0 \text{ V} \end{cases}$	0.1 0.5	200	ns μC Α	

Terminals: 1 - Gate 2 - Drain (Collector) 3 - Source (Emitter)

MYZ	INCHES		MILLIMETERS	
2114	MIN	MAX	MIN	MAX
Α	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
С	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
е	.100 BSC		2.54	BSC
Н	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØΡ	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

Notes:

- 1) Pulse test, t \leq 300 μ s, duty cycle d \leq 2 %
- 2) Test current I_{τ} = 2.5 A

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.